



## IXFX520N075T2 Information



For Reference Only

Part Number IXFX520N075T2

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 75V 520A PLUS247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

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# **IXFX520N075T2 Specifications**

Manufacturer Part Number         IXFX520N075T2           Manufacturer         IXYS           Category         Discrete Semiconductor Products		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-247-3           Series         GigaMOS?, TrenchT2?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         75V           Current - Continuous Drain (Id) @ 25°C         520A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 8mA           Gate Charge (Qg) (Max) @ Vgs         545nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         41000pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         1250W (Tc)           Rds On (Max) @ Id, Vgs         2.2 mOhm @ 100A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PLUS247?-3           Package / Case         TO-247-3	Manufacturer Part Number	IXFX520N075T2
Package         TO-247-3           Series         GigaMOS?, TrenchT2?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         75V           Current - Continuous Drain (Id) @ 25°C         520A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 8mA           Gate Charge (Qg) (Max) @ Vgs         545nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         41000pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         1250W (Tc)           Rds On (Max) @ Id, Vgs         2.2 mOhm @ 100A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PLUS247?-3           Package / Case         TO-247-3	Manufacturer	IXYS
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SeriesGigaMOS?, TrenchT2?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C520A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 8mAGate Charge (Qg) (Max) @ Vgs545nC @ 10VInput Capacitance (Ciss) (Max) @ Vds41000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1250W (Tc)Rds On (Max) @ Id, Vgs2.2 mOhm @ 100A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePLUS247?-3Package / CaseTO-247-3		Transistors - FETs, MOSFETs - Single
FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  75V  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  2.2 mOhm @ 100A, 10V  Operating Temperature  Mounting Type  Supplier Device Package  PLUS247-3  Package / Case	Package	TO-247-3
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  PLUS247?-3  Package / Case  MOSFET (Metal Oxide)  MOSFET (Metal Oxide)  75V  MOSFET (Metal Oxide)  75V  75V  75V  75V  75V  75V  75V  75	Series	GigaMOS?, TrenchT2?
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  520A (Tc)  520A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  5V @ 8mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  For Carlon (Trough Hole  Supplier Device Package  PLUS247?-3  Package / Case  F20A (Tc)  520A (Tc)  5	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  SV @ 8mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  2.2 mOhm @ 100A, 10V  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  PLUS247?-3  Package / Case  520A (Tc)  520A (Tc)  520A (Tc)  520A (Tc)  520A (Tc)  540A  55°C ~ 10V  41000pF @ 25V  41000pF @ 25V  420V  FET Feature  - Case  FET F	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  5V @ 8mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  2.2 mOhm @ 100A, 10V  Operating Temperature  Foreign Through Hole  Supplier Device Package  PLUS247?-3  Package / Case  10V  41000pF @ 25V	Drain to Source Voltage (Vdss)	75V
Vgs(th) (Max) @ Id       5V @ 8mA         Gate Charge (Qg) (Max) @ Vgs       545nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       41000pF @ 25V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       1250W (Tc)         Rds On (Max) @ Id, Vgs       2.2 mOhm @ 100A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       PLUS247?-3         Package / Case       TO-247-3	Current - Continuous Drain (Id) @ 25°C	520A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  41000pF @ 25V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  2.2 mOhm @ 100A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PLUS247?-3  Package / Case  TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  41000pF @ 25V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  2.2 mOhm @ 100A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PLUS247?-3  Package / Case  TO-247-3	Vgs(th) (Max) @ Id	5V @ 8mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1250W (Tc)Rds On (Max) @ Id, Vgs2.2 mOhm @ 100A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePLUS247?-3Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	545nC @ 10V
FET Feature - Power Dissipation (Max) 1250W (Tc) Rds On (Max) @ Id, Vgs 2.2 mOhm @ 100A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	41000pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  2.2 mOhm @ 100A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PLUS247?-3  Package / Case  TO-247-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs2.2 mOhm @ 100A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePLUS247?-3Package / CaseTO-247-3	FET Feature	-
Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PLUS247?-3  Package / Case  TO-247-3	Power Dissipation (Max)	1250W (Tc)
Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	2.2 mOhm @ 100A, 10V
Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	PLUS247?-3
Report errors?	Package / Case	TO-247-3
		Report errors?

#### IXFX520N075T2 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **IXFX520N075T2 Payment Methods**



















## **IXFX520N075T2 Shipping Methods**













If you have any question about IXFX520N075T2, please do not hesitate to contact us!

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